

AMENDMENTS

In the Claims:

Please amend claim 1 as follows.

Sub
figs. 1, 9
B

1. (Twice Amended) A semiconductor device comprising a plurality of semiconductor elements, each being provided with a source region having a source terminal and a drain region having a drain terminal in a well formed in a semiconductor layer, and a gate terminal fabricated on a channel region which receives a first input signal, wherein [the channel region] is formed between said source region and drain region and [receives the first input signal through a gate insulating film], wherein:

each of said semiconductor elements is electrically separated from the others;

said well in each of said semiconductor elements is provided with a substrate terminal which receives a second input signal through a contact hole formed therein at a region other than said source region and drain region; and

the first and second input signals are different signals that are synchronized with each other.

9, 16